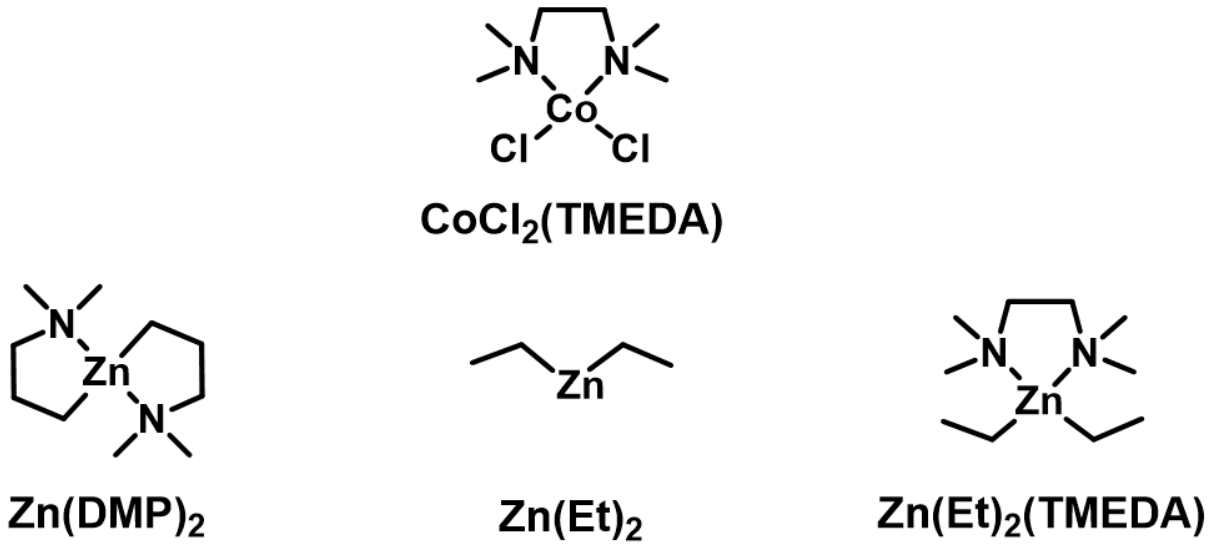

Figure 1: Schematic structures of the Co precursor $CoCl_2$(TMEDA) and potential Zn dialkyl co-reactants namely $Zn(DMP)_2$, $Zn(Et)_2$ and $Zn(Et)_2$(TMEDA).

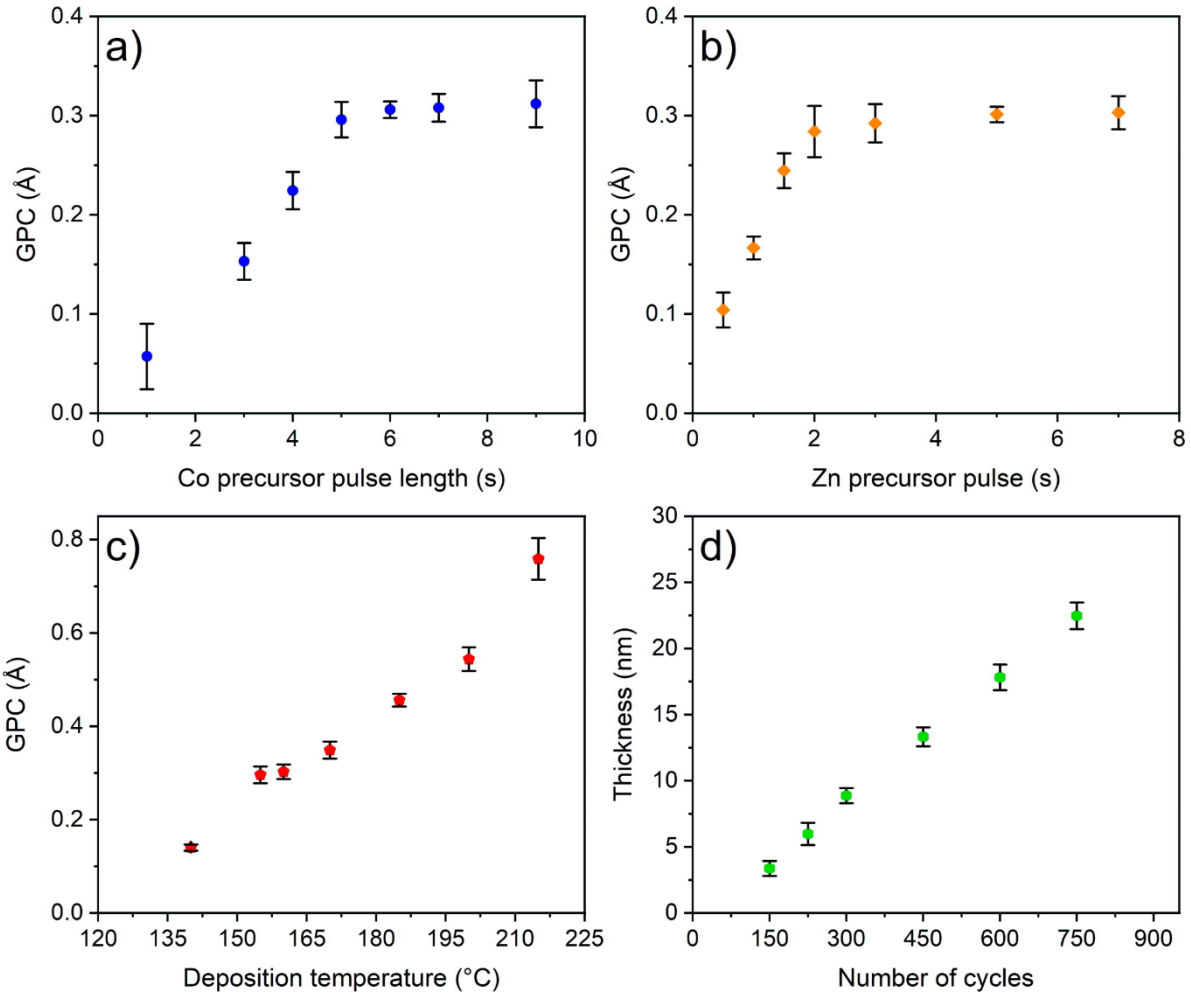

Figure 2: Characteristics of the ALD process using $CoCl_2$(TMEDA) and $Zn(DMP)_2$ on Si(100) substrates: a) $CoCl_2$(TMEDA) saturation study and b) $Zn(DMP)_2$ saturation investigation at 155 °C each. c) Temperature dependency of the GPC. d) Linear dependency of the film thickness on the applied number of cycles at 155 °C utilizing optimized process parameters. Film thicknesses were determined by XRR measurements.